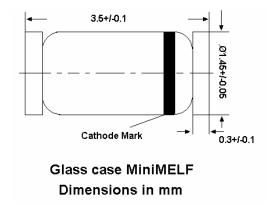
## SILICON EPITAXIAL PLANAR DIODE

## **Features**

- Fast Switching Speed
- High Reliability
- **High Conductance**
- For General Purpose Switching Applications

LL-34



## Absolute Maximum Ratings (T<sub>a</sub> = 25°C)

Characteristic	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	$V_{RM}$	50	V
Forward Continuous Current (Note 1)	I <sub>FM</sub>	400	mA
Average Rectified Output Current (Note 1)	Io	300	mA
Power Dissipation (Note 1) Derate Above 25°C	P <sub>tot</sub>	500 1.68	mW mW/°C
Junction temperature	T <sub>J</sub>	200	°С
Operating and Storage Temperature Range	T <sub>STG</sub>	-65 to +175	оС

## Characteristics at $T_j = 25^{\circ}C$

Characteristic	Symbol	Min.	Max.	Unit
Forward Voltage at I <sub>F</sub> = 300mA	V <sub>F</sub>	-	1.2	٧
Peak Reverse Current at $V_R = 50V$	I <sub>R</sub>	-	100	nA
Reverse Recovery Time at $I_F = I_R = 10$ to 200mA, to 0.1 $I_F$	T <sub>RR</sub>	-	4	nS







